

# SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

# N-Channel Silicon MOSFET **CPH6445** — General-Purpose Switching Device **Applications**

# **Features**

- 4V drive
- · Low ON-resistance
- · Protection diode in

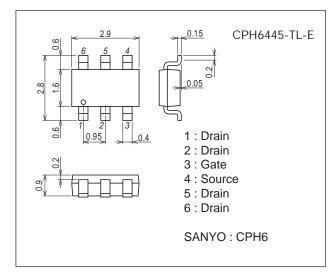
# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		60	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		3.5	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	14	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm <sup>2</sup> x0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

# Package Dimensions

unit : mm (typ) 7018A-003



### **Product & Package Information**

Package

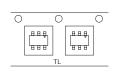
• JEITA, JEDEC

: CPH6 : SC-74, SOT-26, SOT-457

Marking

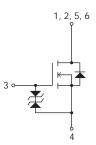
• Minimum Packing Quantity : 3,000 pcs./reel

#### Packing Type: TL





#### **Electrical Connection**

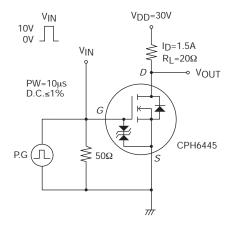


#### SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

Parameter	Cumbal	Conditions		11-14			
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	VDS=10V, ID=1.5A	1.2	2.0		S	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	ID=1.5A, VGS=10V		92	117	mΩ	
	R <sub>DS</sub> (on)2	ID=0.7A, VGS=4.5V		120	168	mΩ	
	R <sub>DS</sub> (on)3	ID=0.7A, VGS=4V		132	185	mΩ	
Input Capacitance	Ciss			310		pF	
Output Capacitance	Coss	VDS=20V, f=1MHz		40		рF	
Reverse Transfer Capacitance	Crss	]		25		рF	
Turn-ON Delay Time	t <sub>d</sub> (on)			6.0		ns	
Rise Time	tr			5.5		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	off) See specified Test Circuit.		27		ns	
Fall Time	tf	]		13		ns	
Total Gate Charge	Qg			6.8		nC	
Gate-to-Source Charge	Qgs V	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A		1.1		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		1.4		nC	
Diode Forward Voltage	V <sub>SD</sub>	IS=3.5A, VGS=0V		0.85	1.2	V	

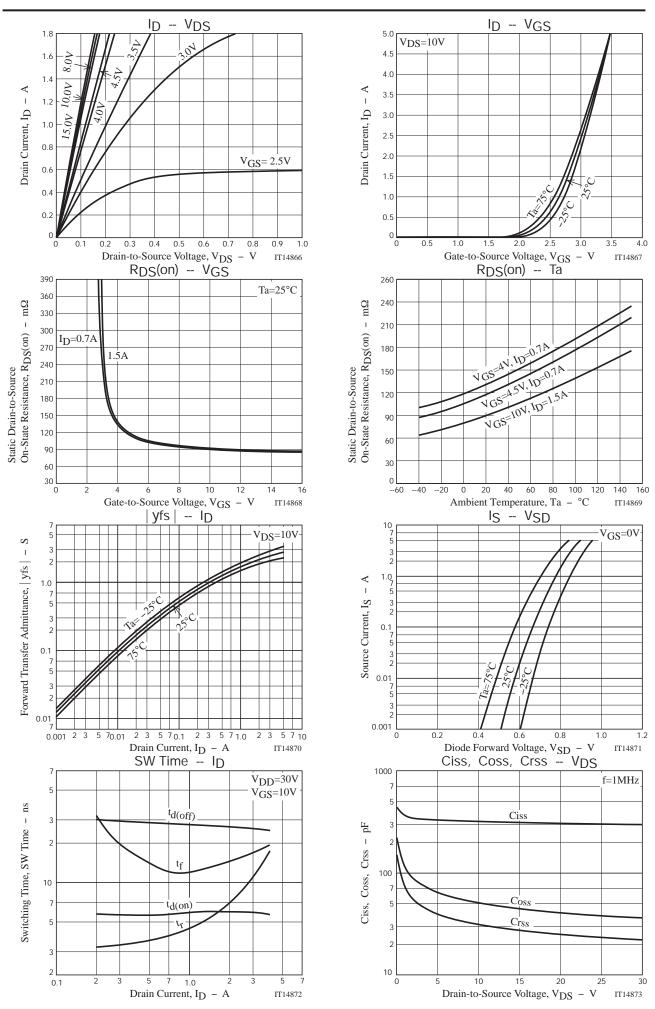
## Electrical Characteristics at Ta=25°C

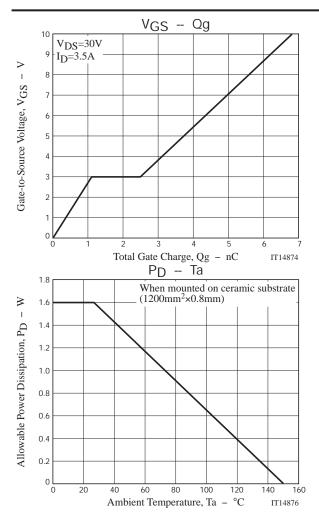
# Switching Time Test Circuit

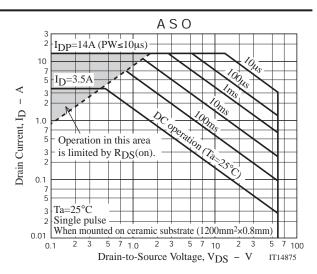


#### **Ordering Information**

Device	Device Package		memo		
CPH6445-TL-E	45-TL-E CPH6		Pb Free		







## Embossed Taping Specification CPH6445-TL-E

1. Packing Format

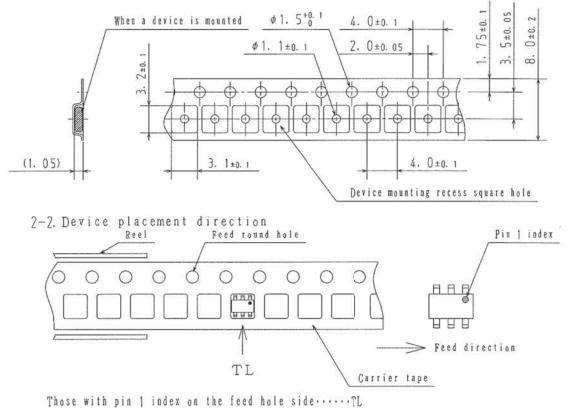
Package Name	Carrier Tape		timum Number of ces contained (pcs)		Packing format					
Type		Reel	eel Inner box Outer box Inner BOX (C-1)			Outer BOX (A-7)				
CPH6	CPH6	3, 000	15, 000	90,000	5 reels contained Dimensions:mm (external) 183×72×185		external)	$\beta$ inner boxes contained Dimensions:mm(external) $440 \times 195 \times 210$		
Packing met	hod		<u>Reel</u>	(u 1	nner box nit:mm) 59		It is a The for	r box label a label at the time of factory shipm m of a label may change in physical bulion process. 108		
	Orig	No. tity		HITHHINI HITHI THINH IN TOP OO HITHINI HITHI ITTY O, OO HITHINI HITHI INTY O, OO HITHINI HITHINI INTY O, OO HITHINI INTY O, OO HITHINI I	COOCO Infilmenta Infilmenta Infilmenta Infilmenta Costa Lock DIFFOSICN: **** REE ¥ desco of the ter	riptiol	0 0 s s s s s s s s s s s s s	TYPE CODE ************************************		
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LEAD FREE 4

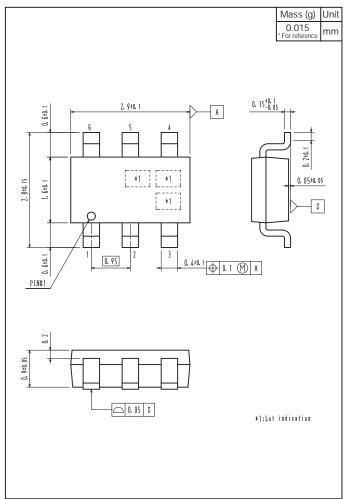
JEITA Phase 3

2. Taping configuration

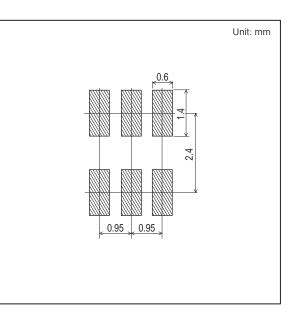
2-1. Carrier tape size (unit:mm)



# Outline Drawing CPH6445-TL-E



# Land Pattern Example



Note on usage : Since the CPH6445 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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